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Kind regards,

Team Nexperia

PDTC124E series

NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

Rev. 8 — 28 November 2011

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET) family in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			PNP	Package
	NXP	JEITA	JEDEC	complement	configuration
PDTC124EE	SOT416	SC-75	-	PDTA124EE	ultra small
PDTC124EM	SOT883	SC-101	-	PDTA124EM	leadless ultra small
PDTC124ET	SOT23	-	TO-236AB	PDTA124ET	small
PDTC124EU	SOT323	SC-70	-	PDTA124EU	very small

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital applications in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



2. Pinning information

Table 3. **Pinning** Simplified outline **Graphic symbol** Pin Description SOT23; SOT323; SOT416 1 input (base) 3 GND (emitter) 2 3 output (collector) 2 006aaa144 sym007 **SOT883** 1 input (base) 2 GND (emitter) output (collector) Transparent

3. Ordering information

Table 4. Ordering information

Type number	Package	Package						
	Name	Description	Version					
PDTC124EE	SC-75	plastic surface-mounted package; 3 leads	SOT416					
PDTC124EM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883					
PDTC124ET	-	plastic surface-mounted package; 3 leads	SOT23					
PDTC124EU	SC-70	plastic surface-mounted package; 3 leads	SOT323					

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTC124EE	06
PDTC124EM	DX
PDTC124ET	*17
PDTC124EU	*06

[1] * = placeholder for manufacturing site code

5. Limiting values

Table 6. Limiting values

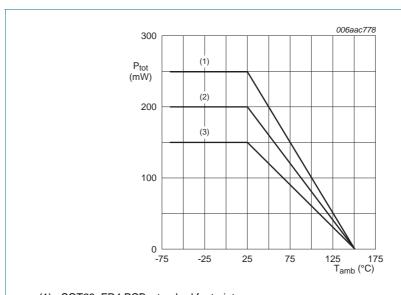
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	10	V
VI	input voltage				
	positive		-	+40	V
	negative		-	-10	V
Io	output current		-	100	mA
I _{CM}	peak collector current	$single \ pulse; \\ t_p \leq 1 \ ms$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PDTC124EE (SOT416)		[1][2]	150	mW
	PDTC124EM (SOT883)		[2][3]	250	mW
	PDTC124ET (SOT23)		[1] -	250	mW
	PDTC124EU (SOT323)		[1] -	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

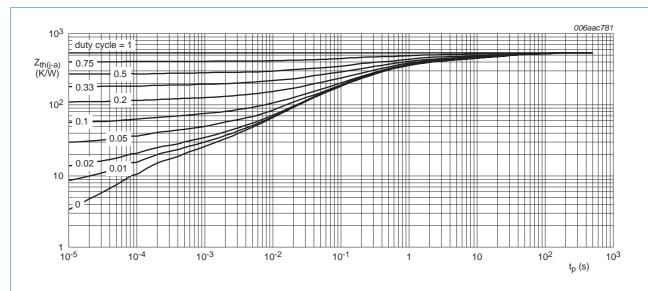
Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

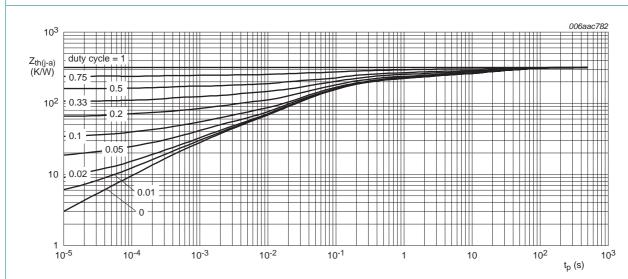
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PDTC124EE (SOT416)		[1][2]	-	830	K/W
	PDTC124EM (SOT883)		[2][3]	-	500	K/W
	PDTC124ET (SOT23)		[1] -	-	500	K/W
	PDTC124EU (SOT323)		<u>[1]</u> _	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC124EE (SOT416); typical values



FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC124EM (SOT883); typical values

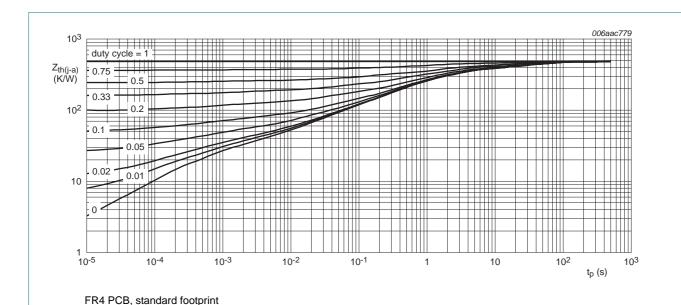


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC124ET (SOT23); typical values

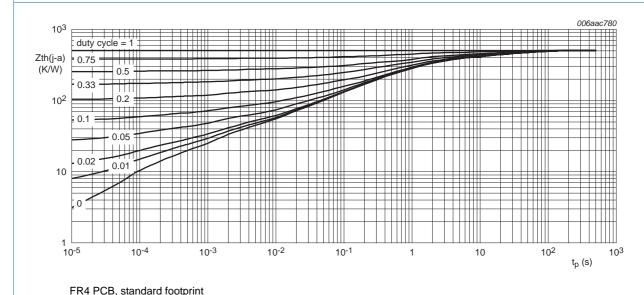


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTC124EU (SOT323); typical values

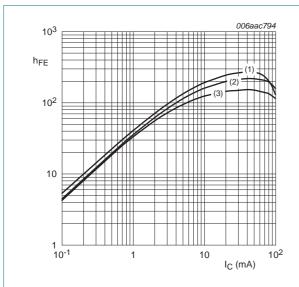
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	100	nA
•	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	180	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	60	-	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	1.1	8.0	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 5 \text{ mA}$	2.5	1.7	-	V
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz	[1] -	230	-	MHz

^[1] Characteristics of built-in transistor



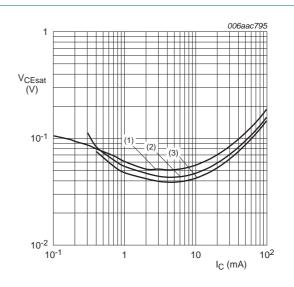
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 6. DC current gain as a function of collector current; typical values



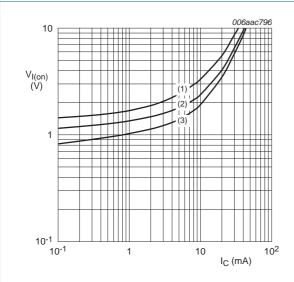
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



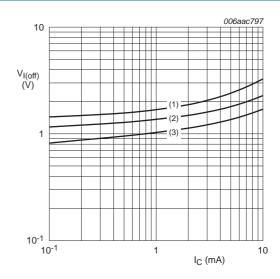
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 8. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 9. Off-state input voltage as a function of collector current; typical values

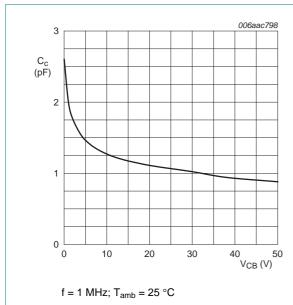


Fig 10. Collector capacitance as a function of collector-base voltage; typical values

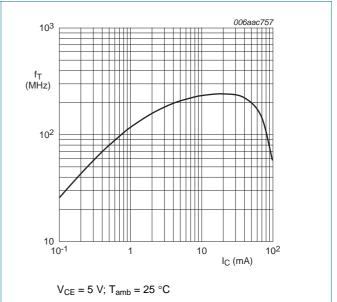


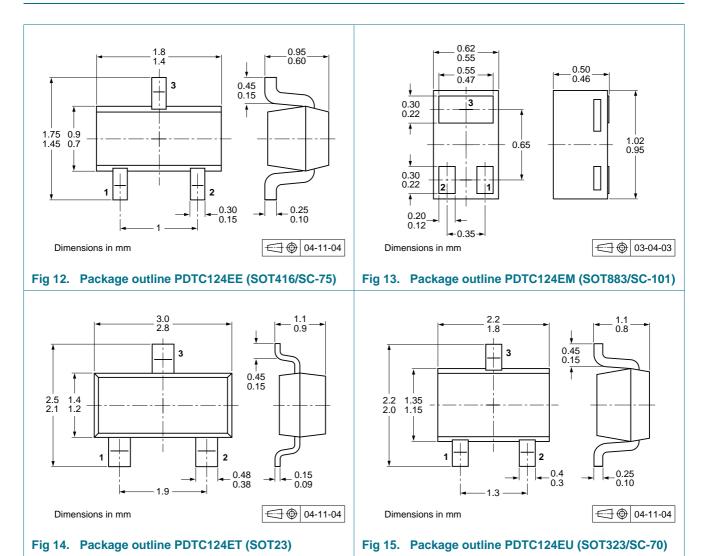
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing qu		uantity		
			3000	5000	10000		
PDTC124EE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135		
PDTC124EM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315		
PDTC124ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235		
PDTC124EU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135		

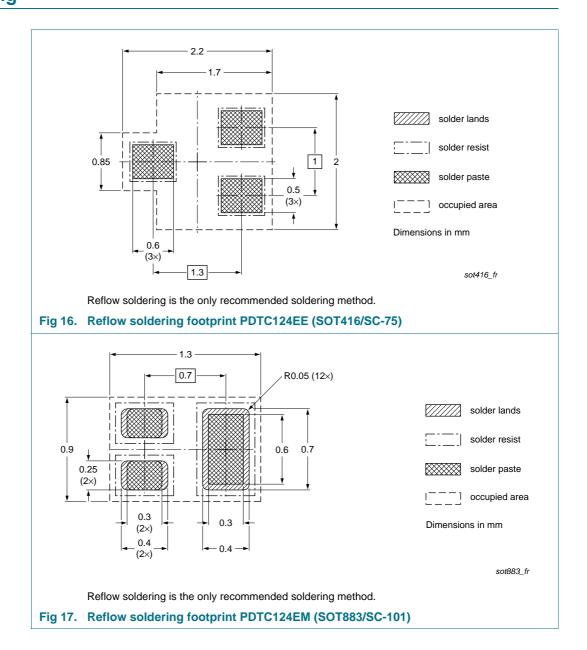
[1] For further information and the availability of packing methods, see Section 14.

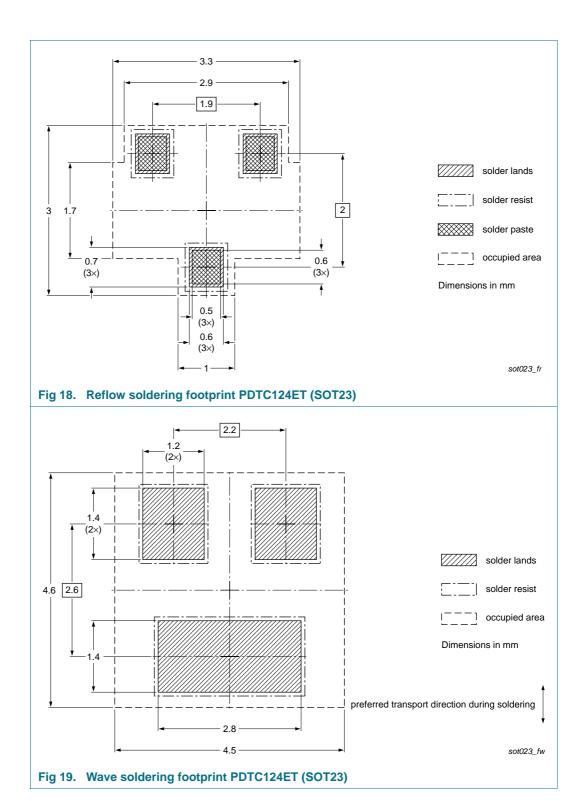
PDTC124E_SER

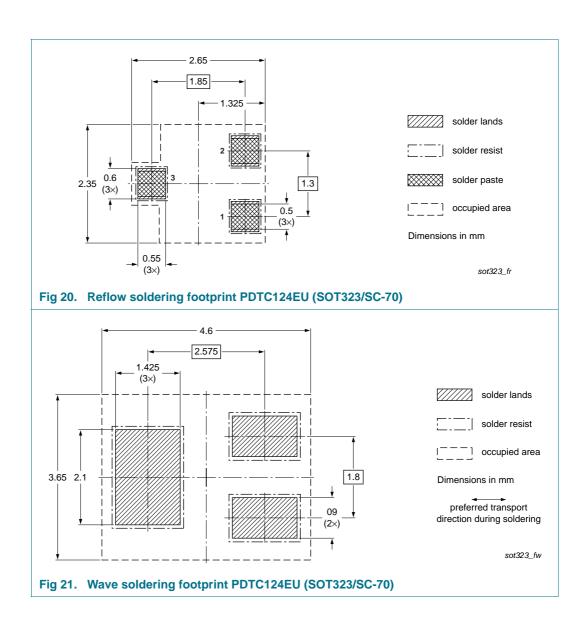
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11. Soldering







12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
PDTC124E_SER v.8	20111128	Product data sheet	-	PDTC124E_SERIES v.7			
Modifications:	guidelines of	of this document has been NXP Semiconductors.		•			
	 Legal texts have been adapted to the new company name where appropriate. Type numbers PDTC124EEF, PDTC124EK and PDTC124ES removed. 						
	 Section 1 "Product profile": updated 						
	 Section 3 "Ordering information": added 						
	• Figure 1 to 11: added						
	 Table 6 "Limiting values": updated 						
	Section 6 "Thermal characteristics": updated						
	 Table 8 "Characteristics": V_{i(on)} redefined to V_{I(on)} on-state input voltage, V_{i(off)} redefined to V_{I(off)} off-state input voltage, I_{CEO} updated, f_T added 						
	Section 8 "Test information": added						
	Section 9 "P	ackage outline": supersede	ed by minimized packag	e outline drawings			
	Section 10 "I	Packing information": adde	ed				
	Section 11 "Soldering": added						
	Section 13 "l	Legal information": updated	d				
PDTC124E_SERIES v.7	20040817	Product data sheet	-	PDTC124E_SERIES v.6			
PDTC124E_SERIES v.6	20030414	Product specification	-	-			

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTC124E_SER

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PDTC124E series

NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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PDTC124E series

NPN resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

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